Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

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Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

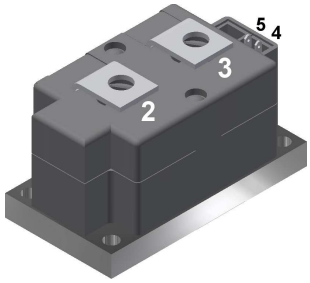
High Voltage Thyristor Module

V_{RRM} = 2000 V
I_{TAV} = 600 A
V_T = 1.06 V

Single Thyristor

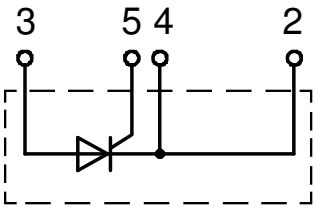
Part number

MCO600-20io1



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

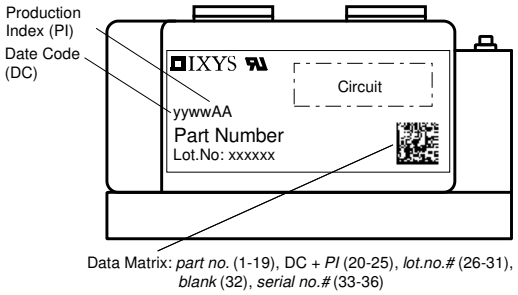
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Thyristor				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			2100	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			2000	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 2000 V	T_{VJ} = 25°C			2	mA
		$V_{R/D}$ = 2000 V	T_{VJ} = 125°C			40	mA
V_T	*forward voltage drop*	I_T = 600 A	T_{VJ} = 25°C			1.12	V
		I_T = 1200 A				1.34	V
		I_T = 600 A	T_{VJ} = 125°C			1.06	V
		I_T = 1200 A				1.33	V
I_{TAV}	*average forward current*	T_C = 85°C	T_{VJ} = 140°C			600	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				940	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 140°C			0.81	V
r_T	*slope resistance* }					0.4	mΩ
R_{thJC}	*thermal resistance junction to case*					0.065	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.020		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			1770	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			15.0	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			16.2	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 140°C			12.8	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			13.8	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.13	MA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.09	MA^2s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 140°C			812.8	kA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			788.8	kA^2s
C_J	*junction capacitance*	V_R = 700 V f = 1 MHz	T_{VJ} = 25°C		469		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 140°C			120	W
		t_P = 300 µs				60	W
P_{GAV}	*average gate power dissipation*					20	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 140°C; f = 50 Hz repetitive,	I_T = 1800 A			100	A/µs
		t_P = 200 µs; di_G/dt = 1 A/µs; I_G = 1 A; V = ⅔ V_{DRM} non-repet.,	I_T = 600 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V = ⅔ V_{DRM}	T_{VJ} = 140°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			2	V
			T_{VJ} = -40°C			3	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			300	mA
			T_{VJ} = -40°C			400	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 140°C			0.25	V
I_{GD}	*gate non-trigger current*					10	mA
I_L	*latching current*	t_p = 30 µs	T_{VJ} = 25°C			400	mA
		I_G = 1 A; di_G/dt = 1 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			300	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 1 A; di_G/dt = 1 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 600 A; V = ⅔ V_{DRM}	T_{VJ} = 125 °C		350		µs
		di/dt = 10 A/µs dv/dt = 50 V/µs t_p = 200 µs					

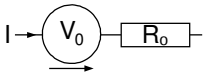
Package Y1				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				600	A
T_{VJ}	*virtual junction temperature*			-40		140	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		125	°C
Weight					650		g
M_D	*mounting torque*			4.5		7	Nm
M_T	*terminal torque*			11		13	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	16.0			mm
$d_{Spb/Apb}$			*terminal to backside*	25.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO600-20io1	MCO600-20io1	Box	3	474320

Equivalent Circuits for Simulation

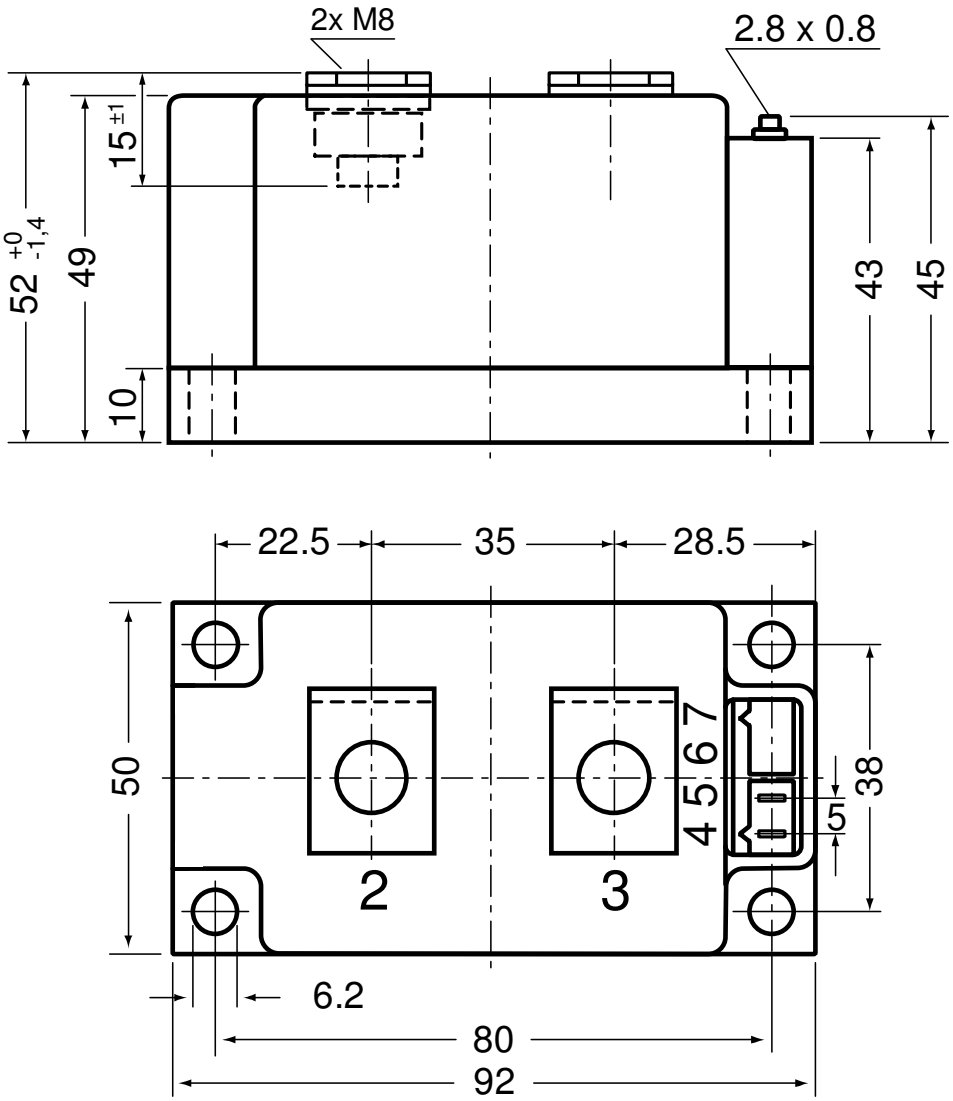
** on die level* T_{VJ} = 140 °C



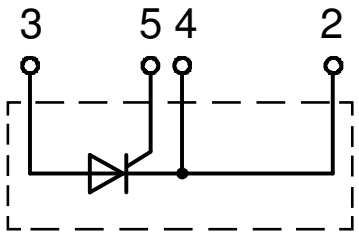
Thyristor

$V_{0\,max}$	*threshold voltage*	0.81	V
$R_{0\,max}$	*slope resistance **	0.22	mΩ

Outlines Y1



Optional accessories for modules
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 180L (L = Left for pin pair 4/5)
Type ZY 180R (R = Right for pin pair 6/7)
} UL 758, style 3751



Thyristor

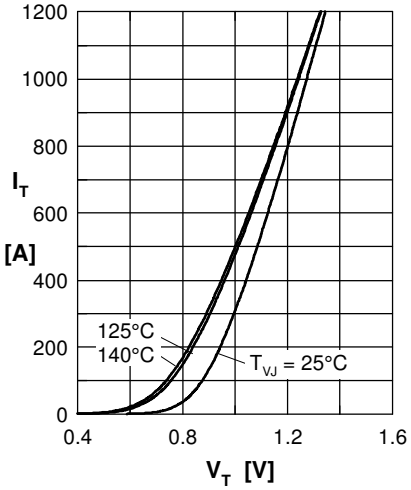


Fig. 1 Forward characteristics

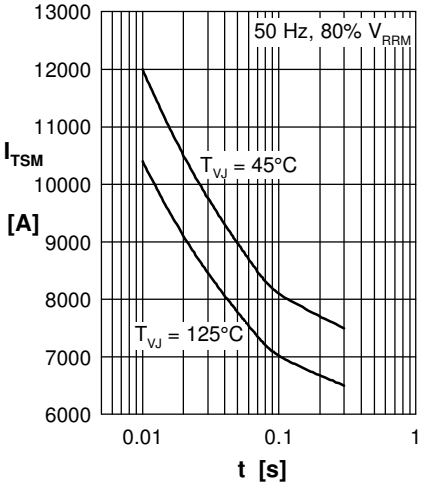


Fig. 2 Surge overload current

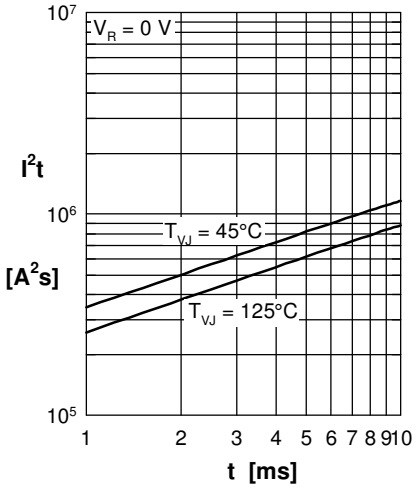


Fig. 3 I^2t versus time (1-10 ms)

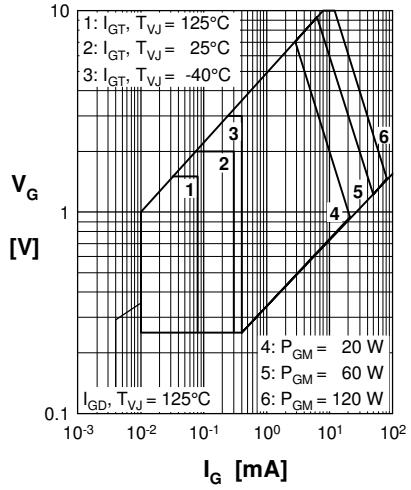


Fig. 4 Gate trigger characteristics

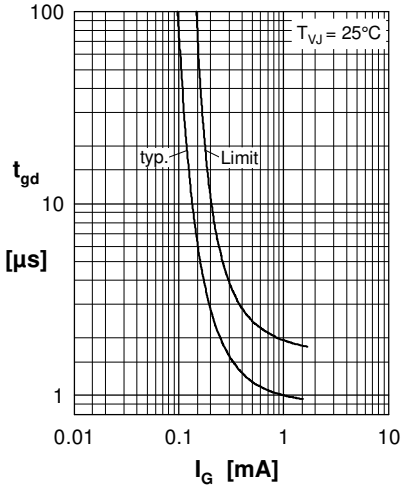


Fig. 5 Gate controlled delay time

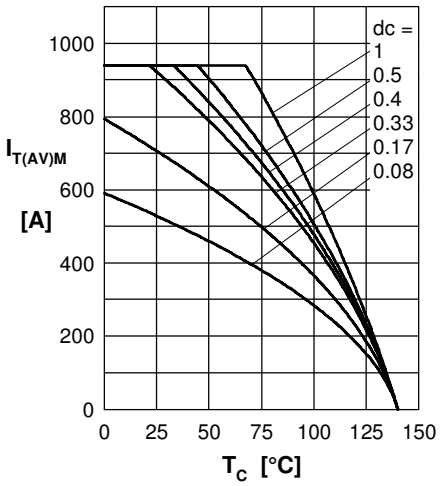


Fig. 6 Max. forward current at case temperature

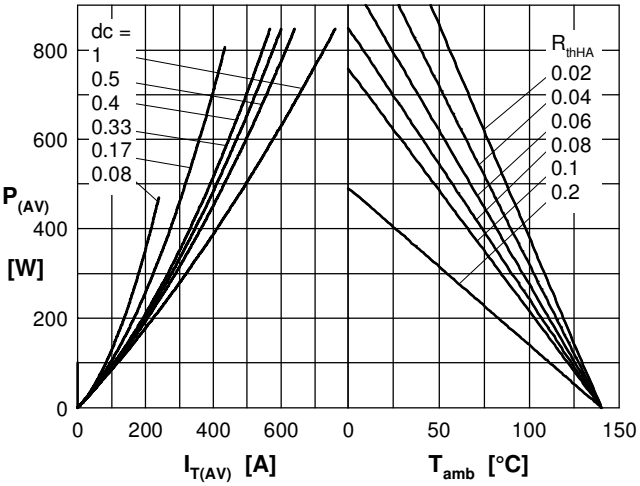


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

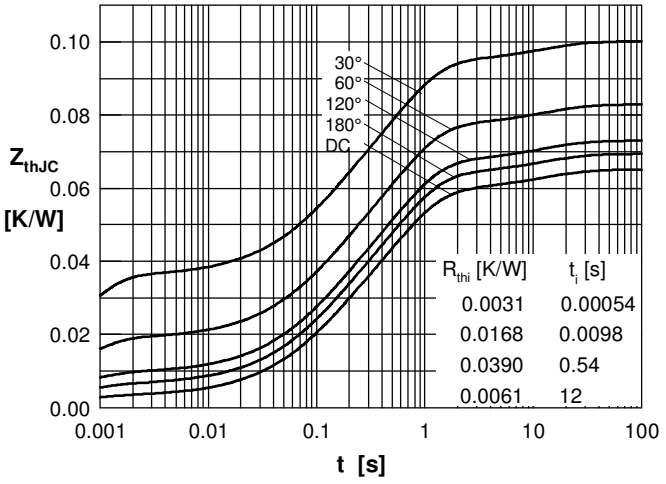


Fig. 8 Transient thermal impedance

IGBT